

Enhancement Mode N-Channel Power MOSFET

Features

- ◆ Ultra-fast and robust body diode
- ◆ Low $R_{DS(on)}$ & FOM
- ◆ Excellent low switching loss
- ◆ Excellent stability and uniformity
- ◆ Easy to drive

Applications

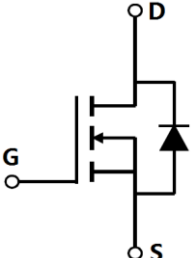
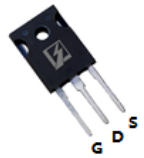
- ◆ PC power
- ◆ Server power supply
- ◆ Telecom
- ◆ Solar inverter
- ◆ Super charger for automobiles

■ General Description

OSG55R030HZF uses advanced GreenMOST[™] technology to provide low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. This device offers extremely fast and robust body diode, and is suitable for telecom and super charger applications.

◆ $V_{DS, \min@T_{jmax}}$	600 V
◆ $I_{D, \text{pulse}}$	240 A
◆ $R_{DS(ON), \text{max @ } V_{GS}=10 \text{ V}}$	30 mΩ
◆ Q_g	177.9 nC

■ Schematic and Package Information

SCHEMATIC DIAGRAM	PIN ASSIGNMENT-TOP VIEW
	 TO247 OSG55R030HZF

■ Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	550	V
Gate source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25^\circ\text{C}$	I_D	80	A
Continuous drain current ¹⁾ , $T_C=100^\circ\text{C}$		50	
Pulsed drain current ²⁾ , $T_C=25^\circ\text{C}$	$I_{D, \text{pulse}}$	240	A
Power dissipation ³⁾ , $T_C=25^\circ\text{C}$	P_D	480	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	2500	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\ldots 440 \text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\ldots 440 \text{ V}$, $I_{SD} \leq I_D$	dv/dt	50	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^\circ\text{C}$

■ Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.26	$^{\circ}\text{C}/\text{W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^{\circ}\text{C}/\text{W}$

■ Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	550			V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
		600	670			$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$, $T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	3		4.5	V	$V_{DS}=V_{GS}$, $I_D=2\text{ mA}$
Drain-source on-state resistance	$R_{DS(on)}$		0.028	0.03	Ω	$V_{GS}=10\text{ V}$, $I_D=40\text{ A}$
			0.058			$V_{GS}=10\text{ V}$, $I_D=40\text{ A}$, $T_j=150^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	I_{DSS}			10	μA	$V_{DS}=550\text{ V}$, $V_{GS}=0\text{ V}$

■ Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		8449.6		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		669.4		pF	
Reverse transfer capacitance	C_{rss}		16.4		pF	
Turn-on delay time	$t_{d(on)}$		52.1		ns	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $R_G=2\ \Omega$, $I_D=40\text{ A}$
Rise time	t_r		105.2		ns	
Turn-off delay time	$t_{d(off)}$		125.7		ns	
Fall time	t_f		4.1		ns	

■ Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		177.9		nC	$I_D=40\text{ A}$, $V_{DS}=400\text{ V}$, $V_{GS}=10\text{ V}$
Gate-source charge	Q_{gs}		37.4		nC	
Gate-drain charge	Q_{gd}		78.4		nC	
Gate plateau voltage	V_{plateau}		6.2		V	

■ Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward current	I_S			80	A	$V_{GS}<V_{th}$
Pulsed source current	I_{SP}			240		
Diode forward voltage	V_{SD}			1.4	V	$I_S=80\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		186.6		ns	$I_S=40\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		1.6		μC	
Peak reverse recovery current	I_{rrm}		15.4		A	

■ Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=100\text{ V}$, $R_G=25\text{ }\Omega$, $L=80\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

■ Electrical Characteristics Diagrams

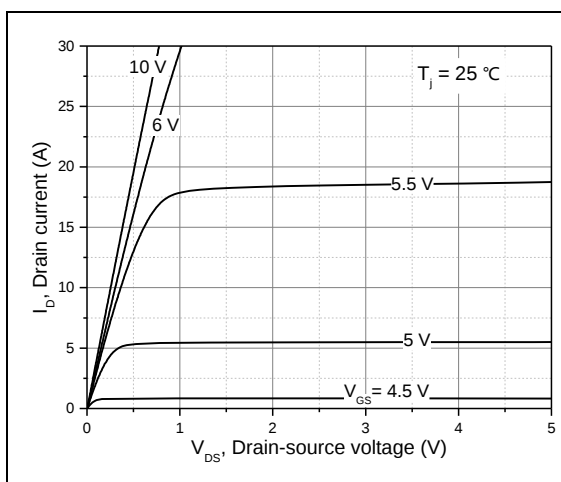


Figure 1, Typ. output characteristics

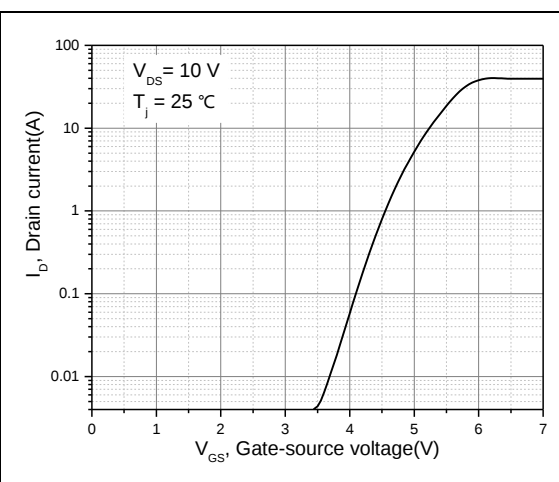


Figure 2, Typ. transfer characteristics

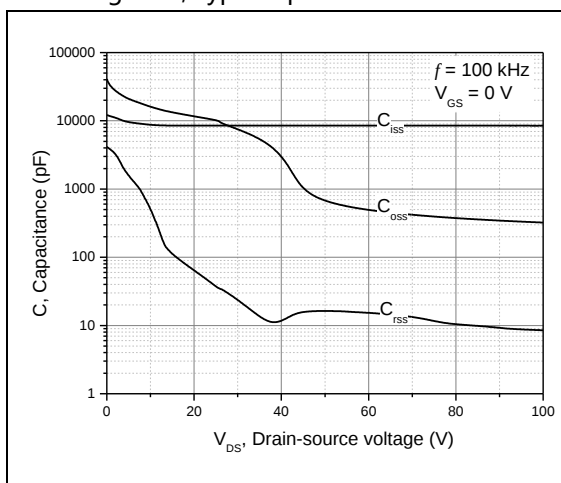


Figure 3, Typ. capacitances

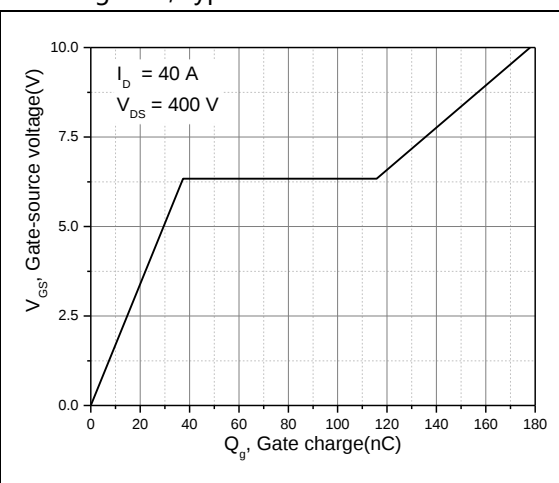


Figure 4, Typ. gate charge

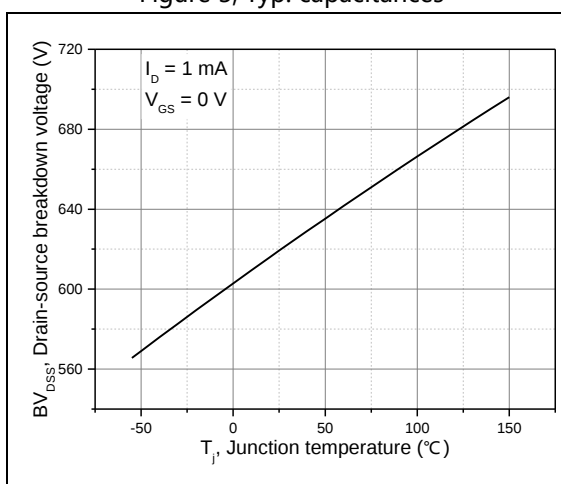


Figure 5, Drain-source breakdown voltage

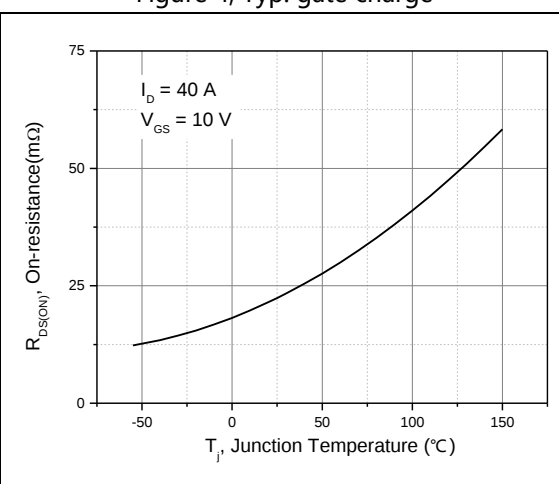


Figure 6, Drain-source on-state resistance

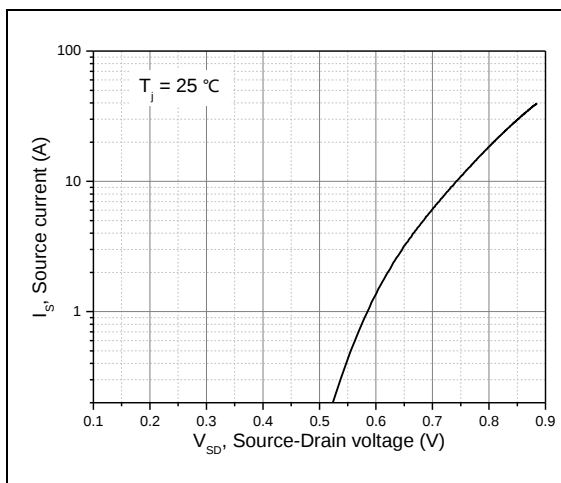


Figure 7, Forward characteristic of body diode

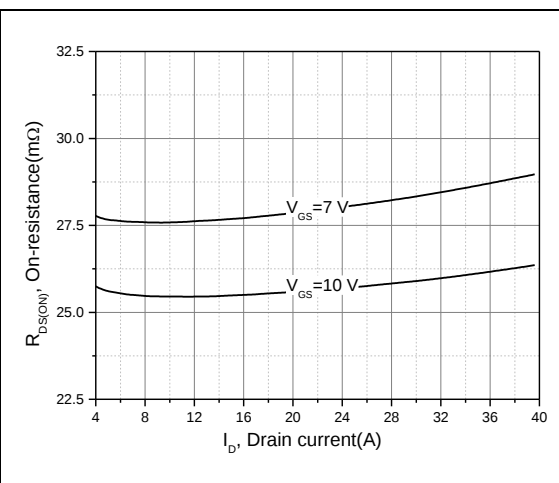


Figure 8, Drain-source on-state resistance

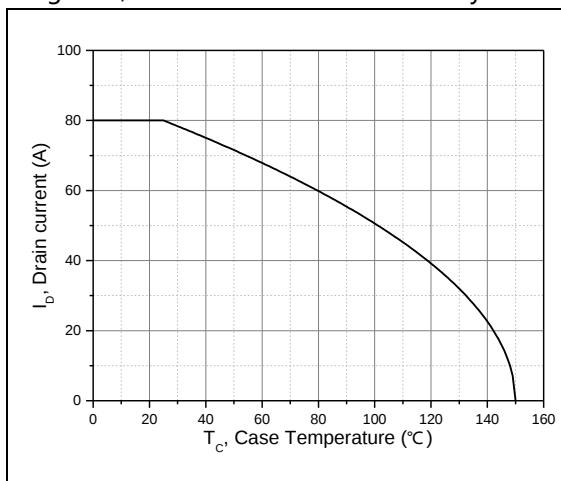


Figure 9, Drain current

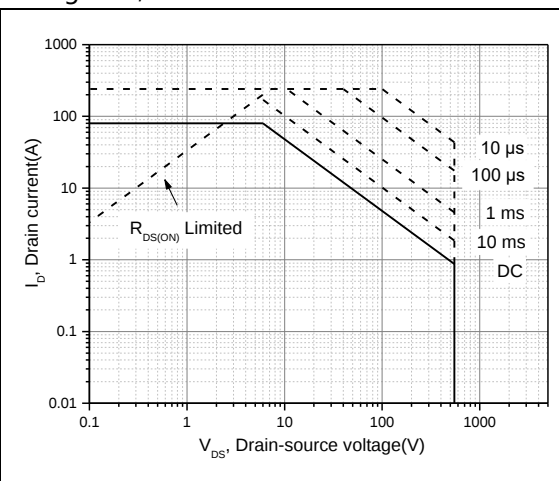


Figure 10, Safe operation area $T_C = 25\text{ }^{\circ}\text{C}$

■ Test circuits and waveforms

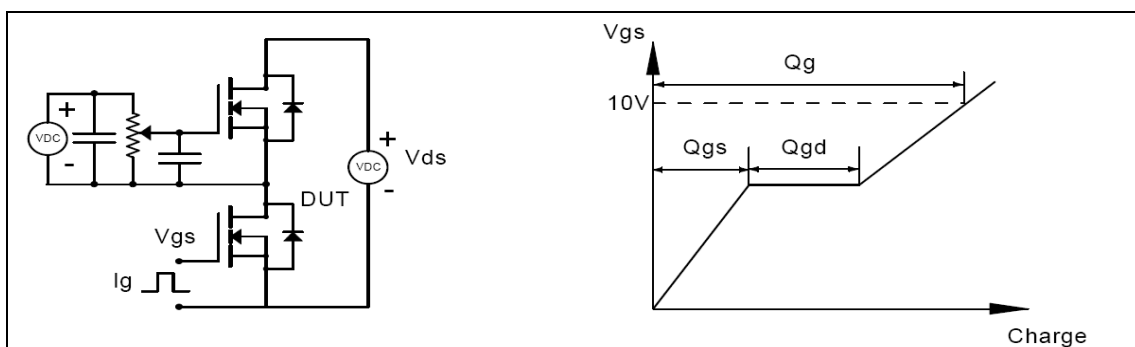


Figure 1, Gate charge test circuit & waveform

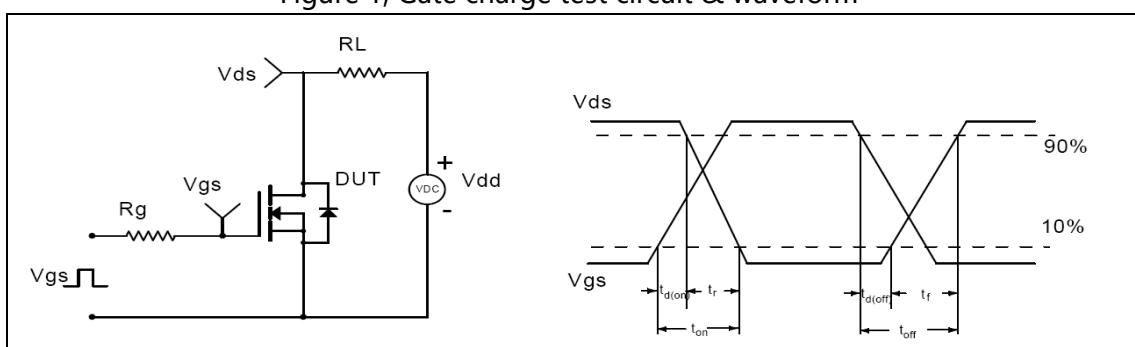


Figure 2, Switching time test circuit & waveforms

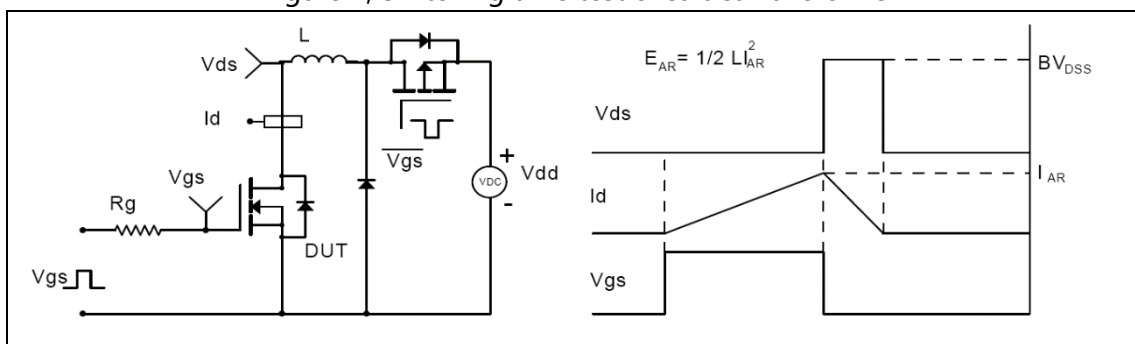


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

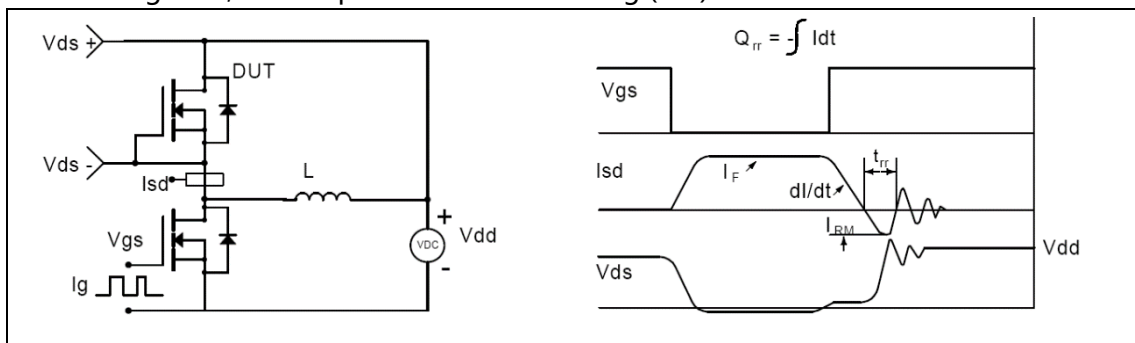
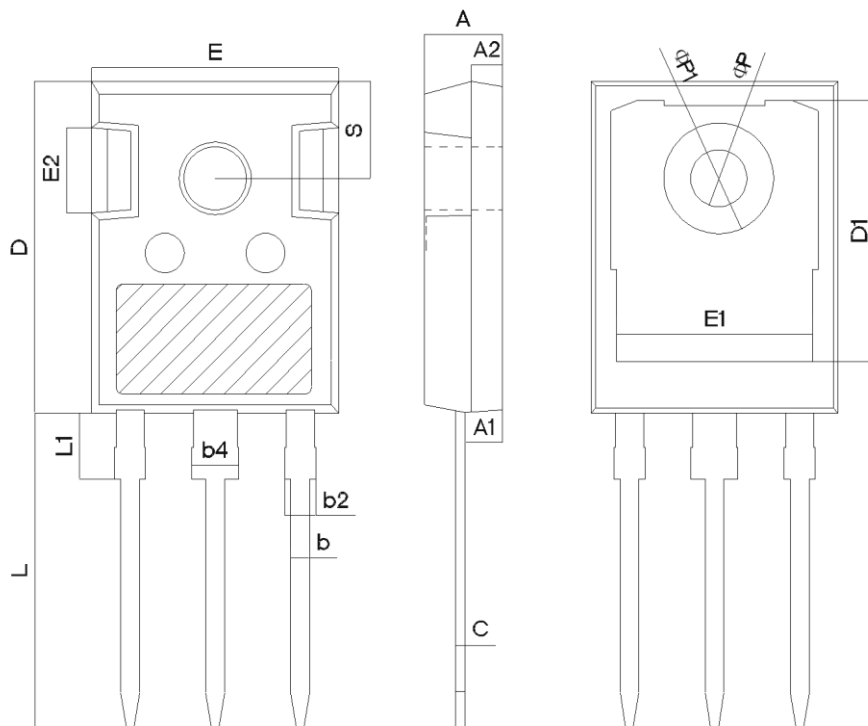


Figure 4, Diode reverse recovery test circuit & waveforms

■ Package Information

Figure1, TO247 package outline dimension



SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.70	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44BSC		
L	19.62	19.92	20.22
L1	-	-	4.30
ΦP	3.40	3.60	3.80
ΦP1	-	-	7.30
S	6.15BSC		

■ Ordering Information

Package	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO247	30	11	330	6	1980

■ Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG55R030HZF	TO247	yes	yes	yes